

BCR20RM-30LA

Triac

Medium Power Use

REJ03G1725-0100 Rev.1.00 Jul 23, 2008

Features

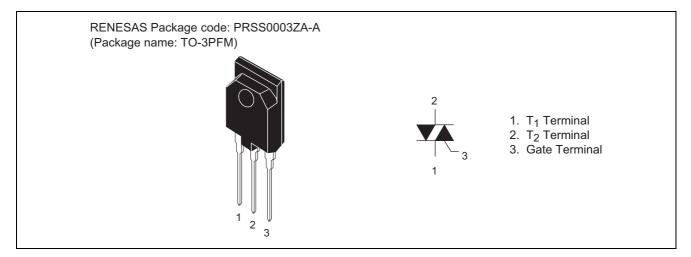
 $\begin{array}{ll} \bullet & I_{T \, (RMS)} : 20 \; A \\ \bullet & V_{DRM} : 1500 \; V \\ \end{array}$

 $\bullet \quad I_{FGTI},\,I_{RGTI},\,I_{RGT\,III}\colon 50\;mA$

Viso: 2000 VInsulated Type

Planar Passivation Type

Outline



Applications

Motor and heater

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
raiametei	Symbol	30		
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	1500	V	
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	1600	V	

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Parameter	Symbo	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	20	А	Commercial frequency, sine full wave 360° conduction, Tc = 83°C
Surge on-state current	I _{TSM}	200	А	50 Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	200	A ² s	Value corresponding to 1 cycle of half wave 50 Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	3	А	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	_	5.2	g	Typical value
Isolation voltage	V _{iso}	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

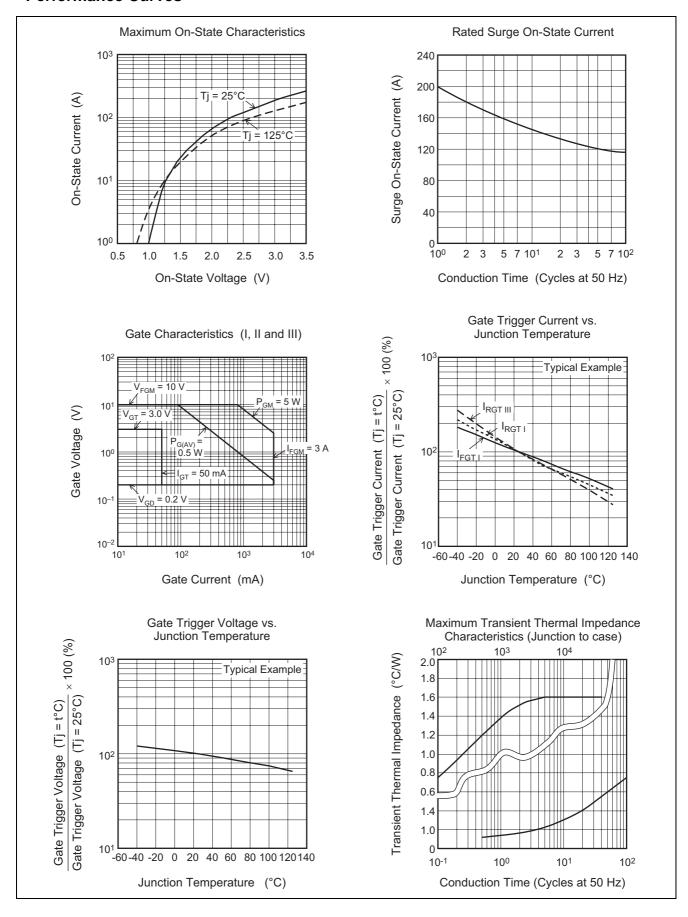
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state cur	rent	I _{DRM}	_	_	10	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V_{TM}		_	1.6	V	Tc = 25°C, I _{TM} = 30 A, Instantaneous measurement
Gate trigger voltage Note2	I	$V_{FGT_{I}}$	_	_	3.0	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	V_{RGTI}	_	_	3.0	V	$R_G = 330 \Omega$
	III	V_{RGTIII}	_	_	3.0	V	
Gate trigger current Note2	I	I _{FGTI}	_	_	50	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	I_{RGTI}		_	50	mA	$R_G = 330 \Omega$
	III	I _{RGTIII}	_	_	50	mA	
Gate non-trigger voltage		V_{GD}	0.2	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	1.6	°C/W	Junction to case Note3
Critical-rate of rise of off-star commutating voltage ^{Note4}	te	(dv/dt)c	20	_	_	V/μs	Tj = 125°C

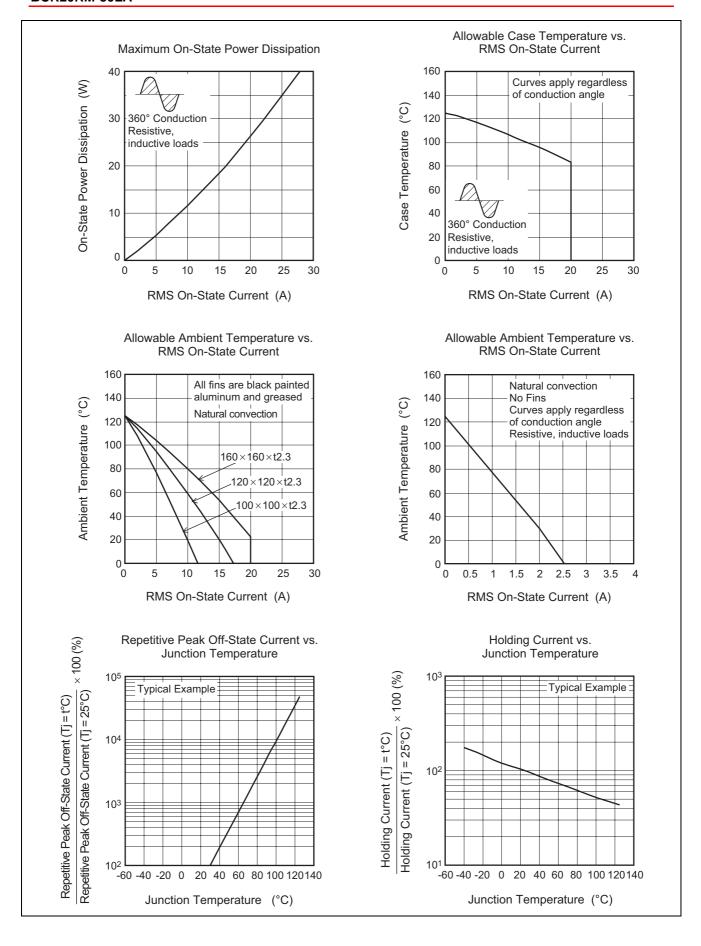
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

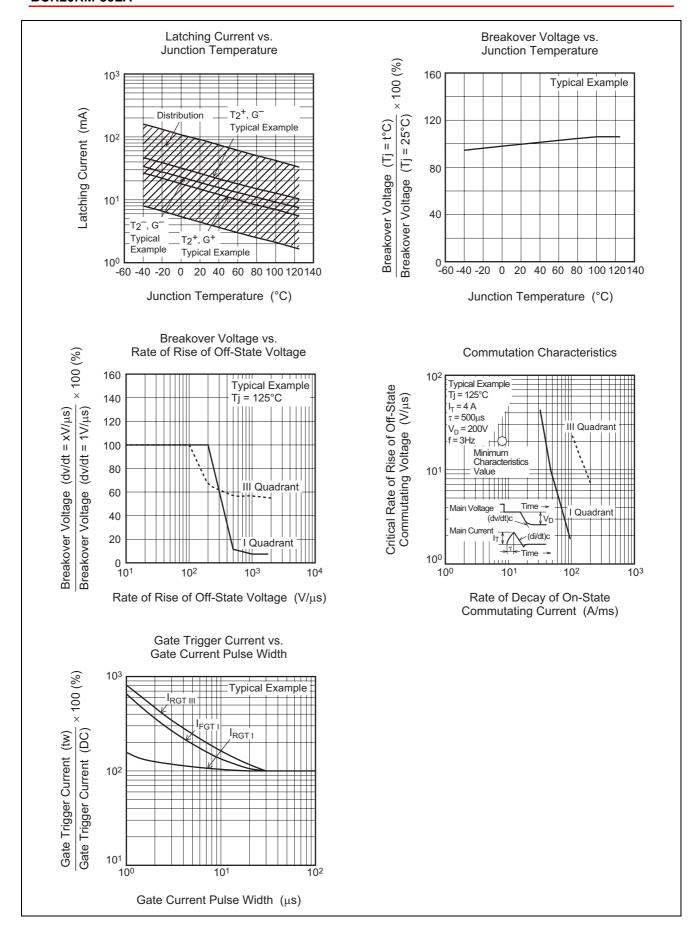
- 3. The contact thermal resistance $R_{th\,(c\text{-}f)}$ in case of greasing is 0.4°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

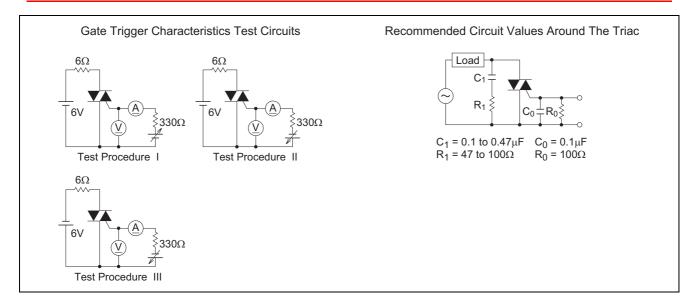
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage → Time
2. Rate of decay of on-state commutating current (di/dt)c = -10 A/ms	Main Current (di/dt)c
3. Peak off-state voltage V _D = 400 V	Main Voltage Time (dv/dt)c

Performance Curves

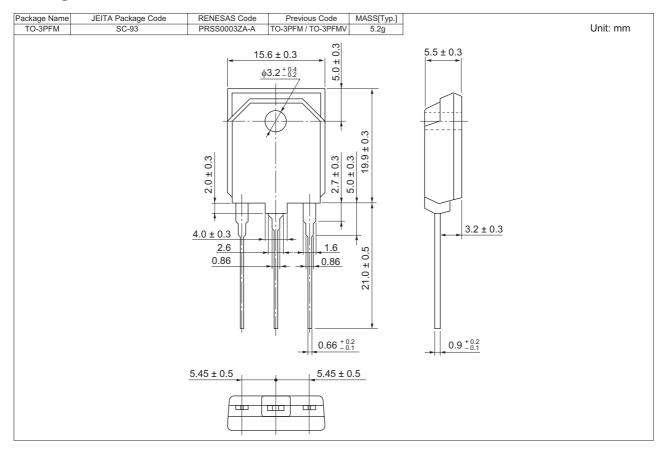








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Magazine (Tube)	30	Type name	BCR20RM-30LA

Note: Please confirm the specification about the shipping in detail.

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